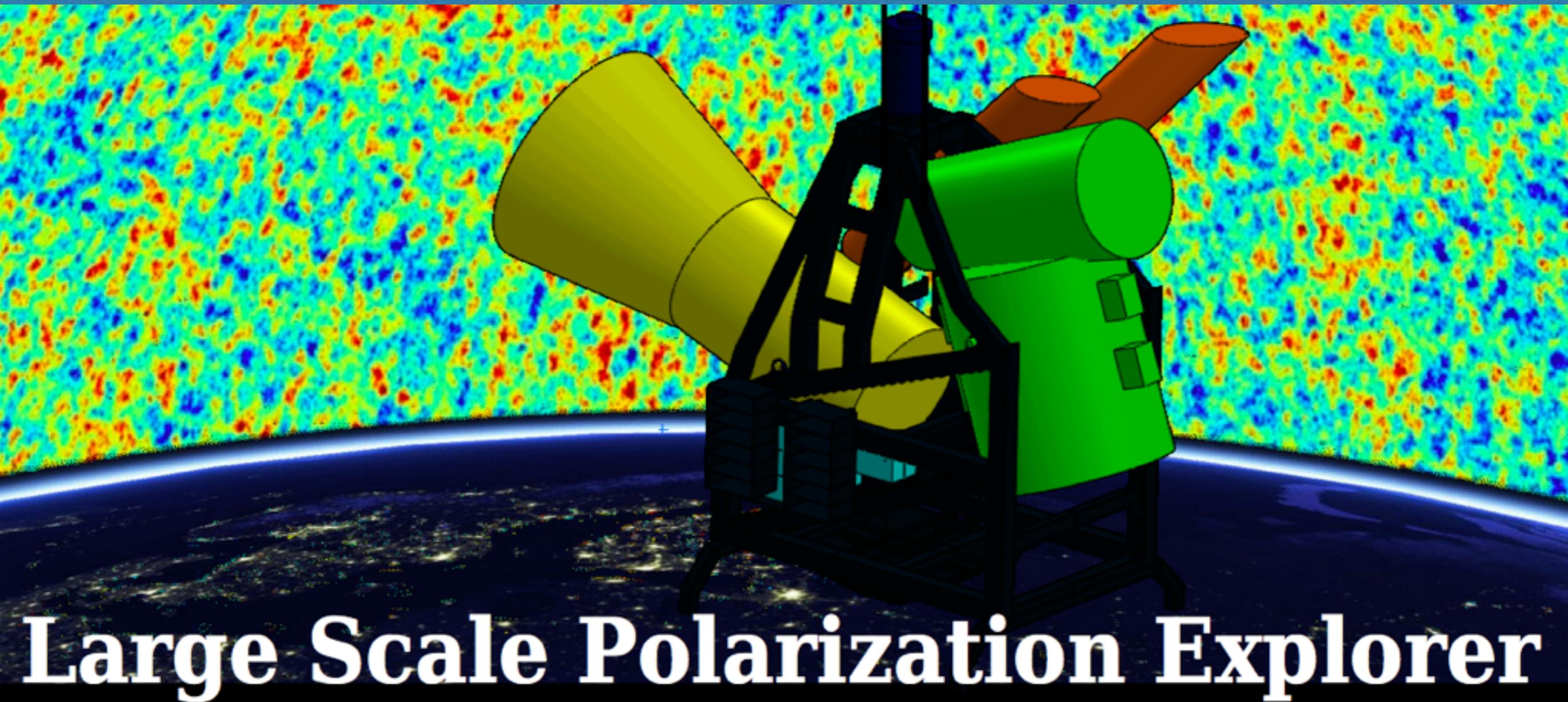


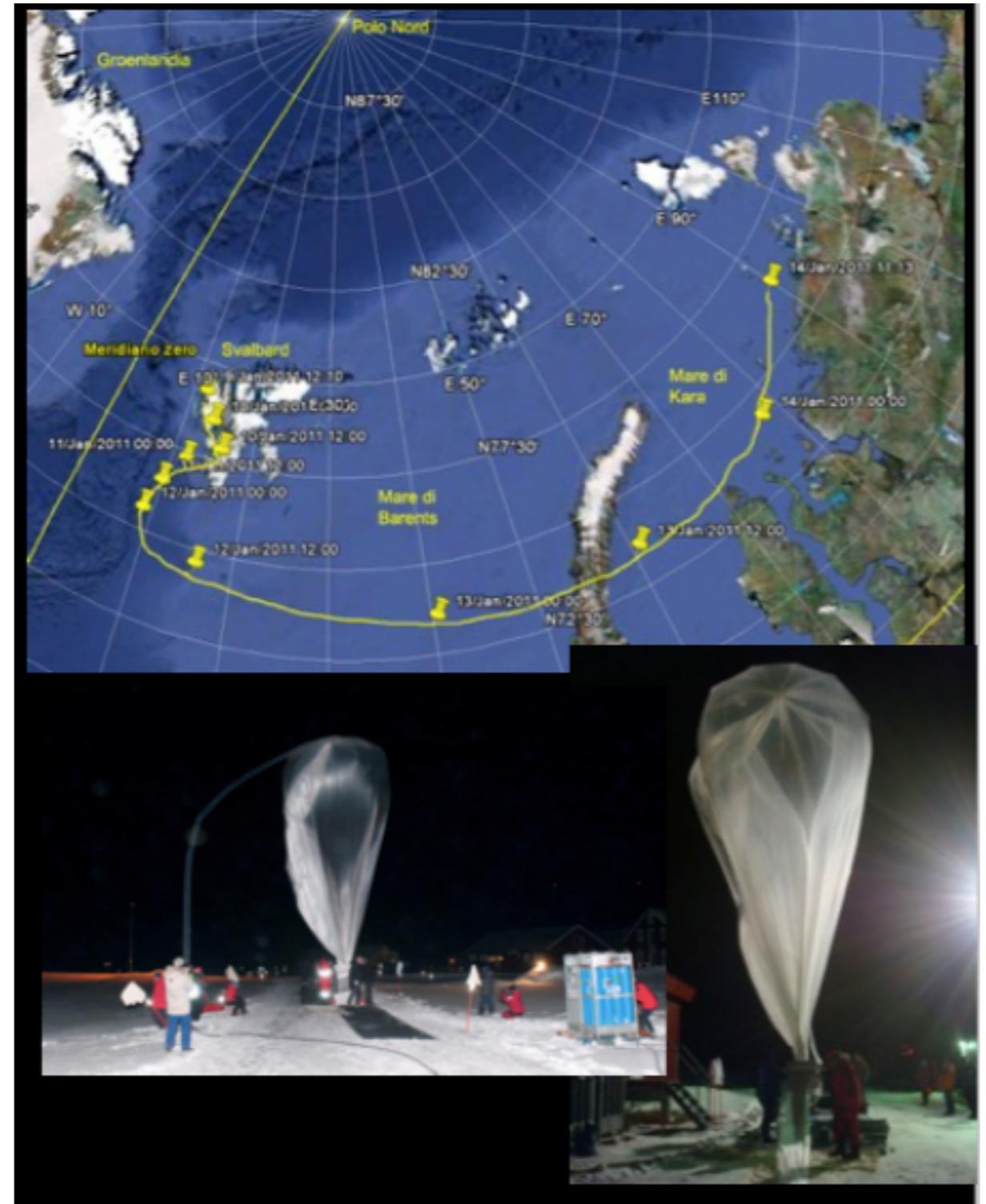
LSPE

Cds Preventivi 2016
Flavio Gatti

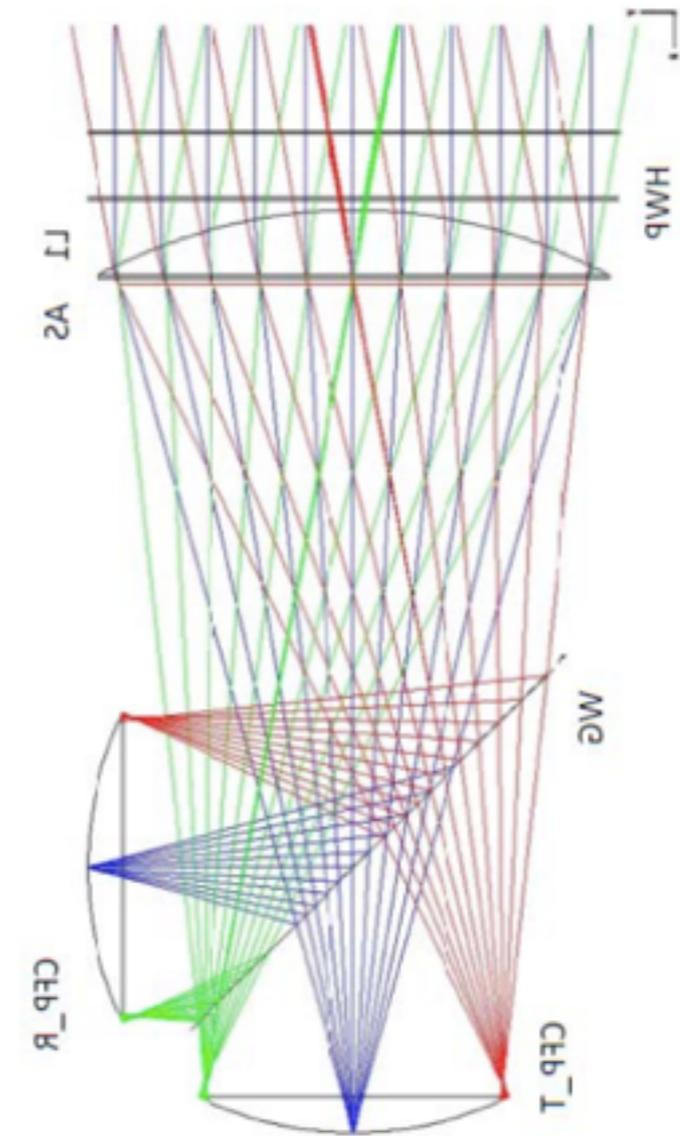
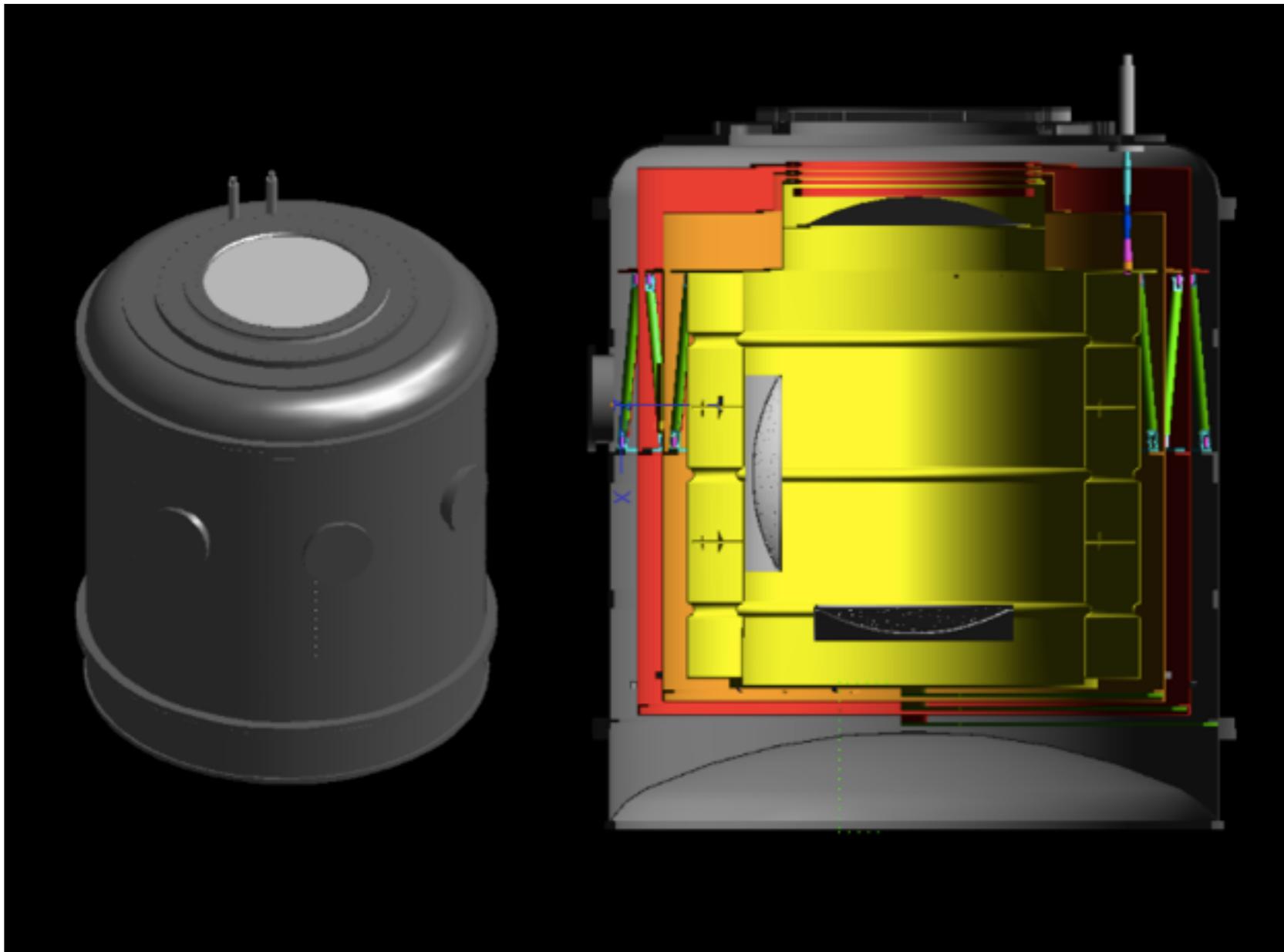


- Genova : Bolometri, LNA, SQUID, Integrazione sul piano focale
- Pisa : Elettronica Frequency Division Multiplexing, Risuonatori
- Roma1: Instrument Design, Criostato, Ottiche, integrazione e test,
- Roma2 : Integrazione e test di pre-volo
- Ferrara : Analisi dati

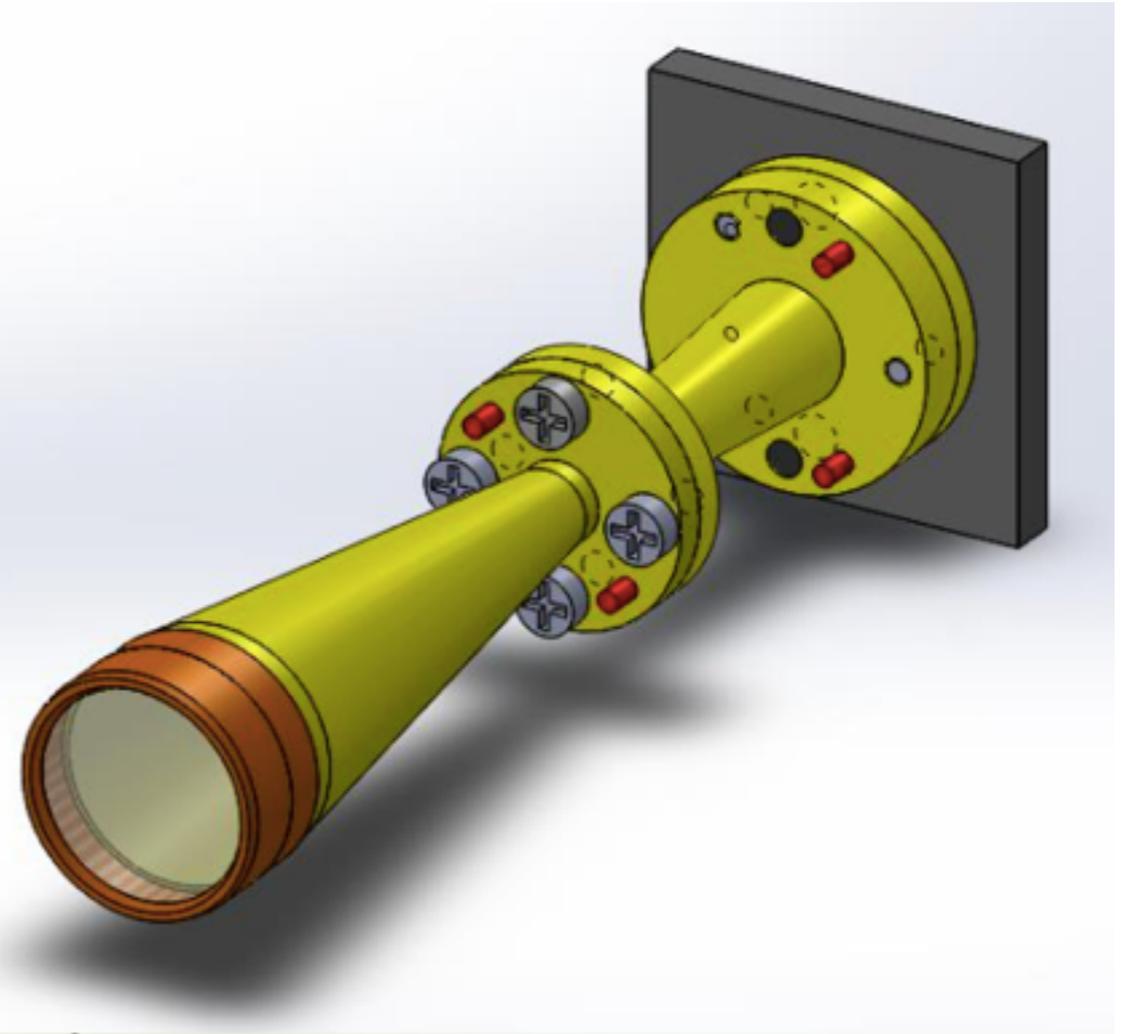
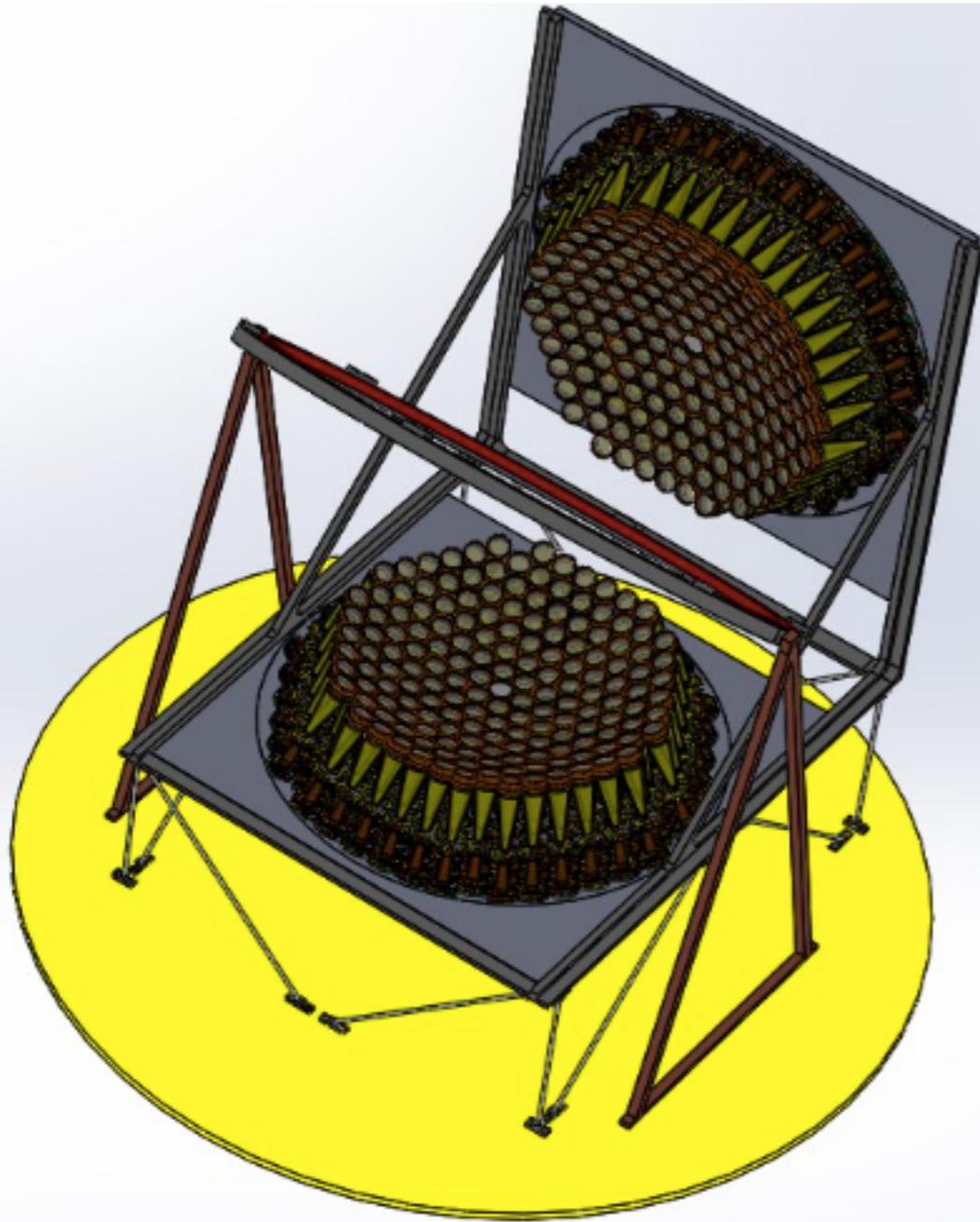
- Volo stratosferico a 30Km: P=3mbar, T=-80C
- Volo notturno: uso batterie termostate per autonomia di 3 settimane (c.a 0.7ton)
- Volo tra 70-80° N
- Pallone 800.000 m³ He gas
- ASI responsabile del lancio e volo
- Gruppo di lavoro coordinato da E.Flamini per utilizzo expertise di altre agenzie alle Svalbard con personale italiano in training
- La data di lancio di gennaio 2016 e spostata a dicembre 2016 - gennaio 2017



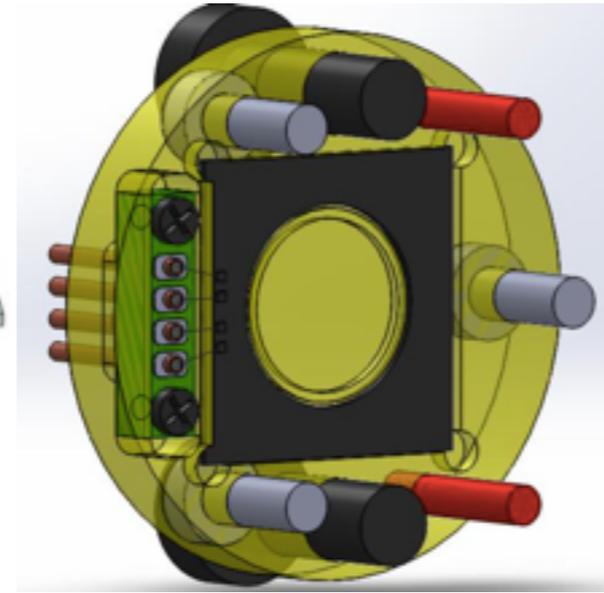
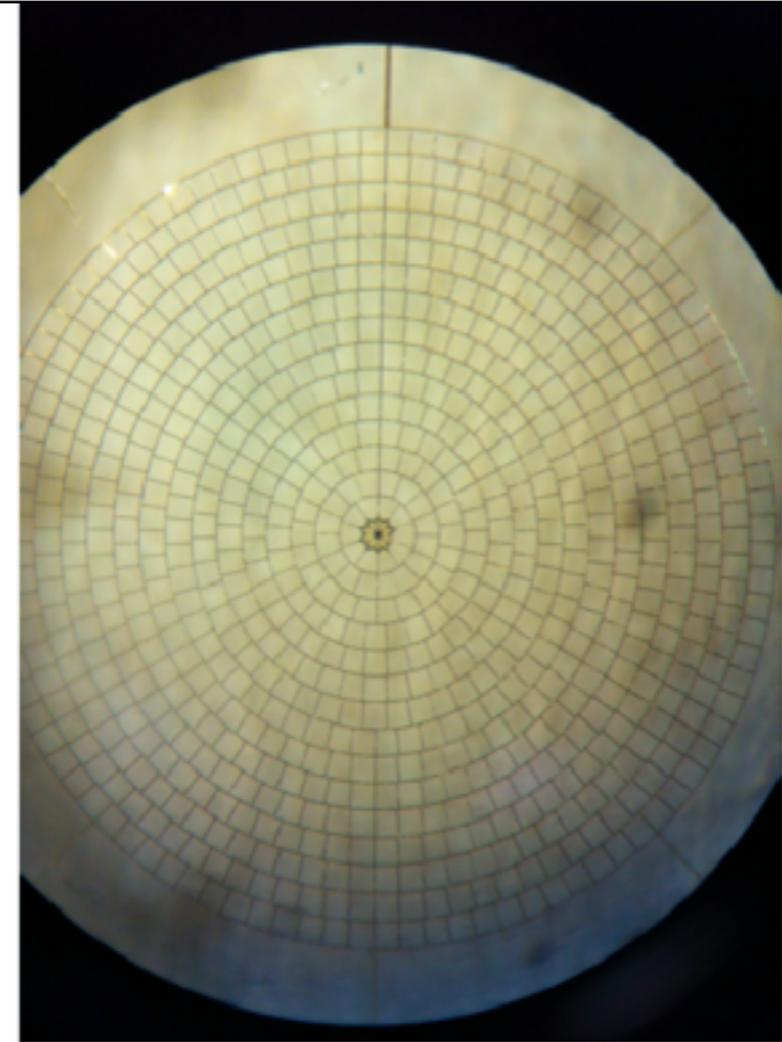
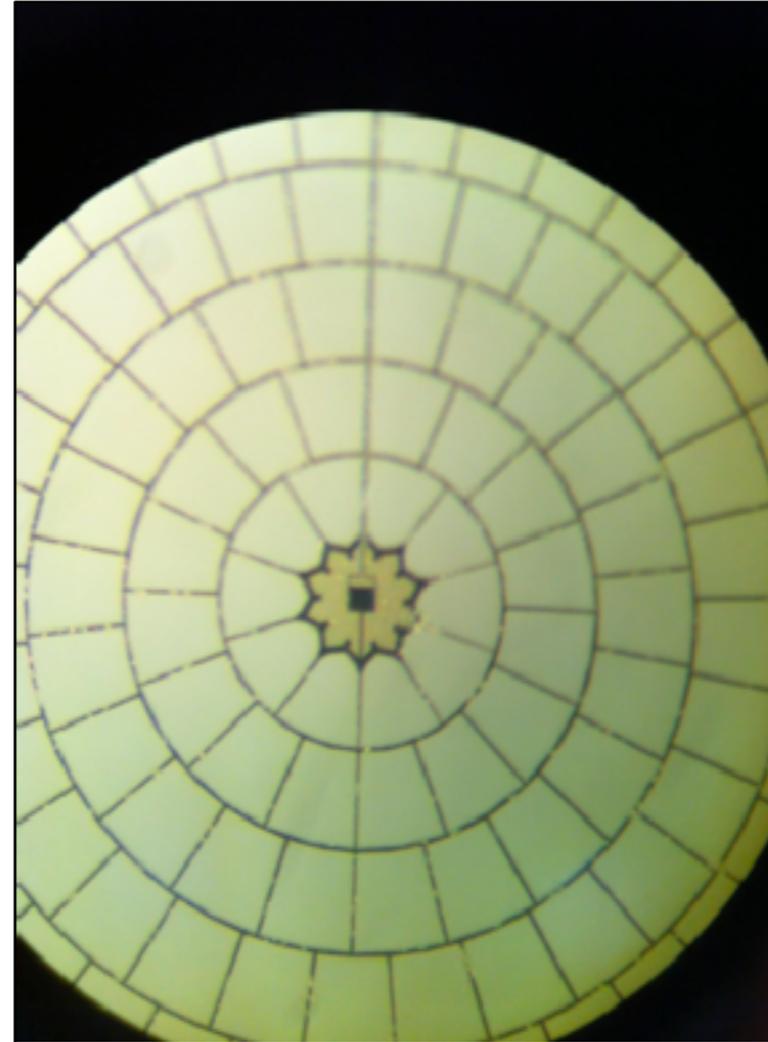
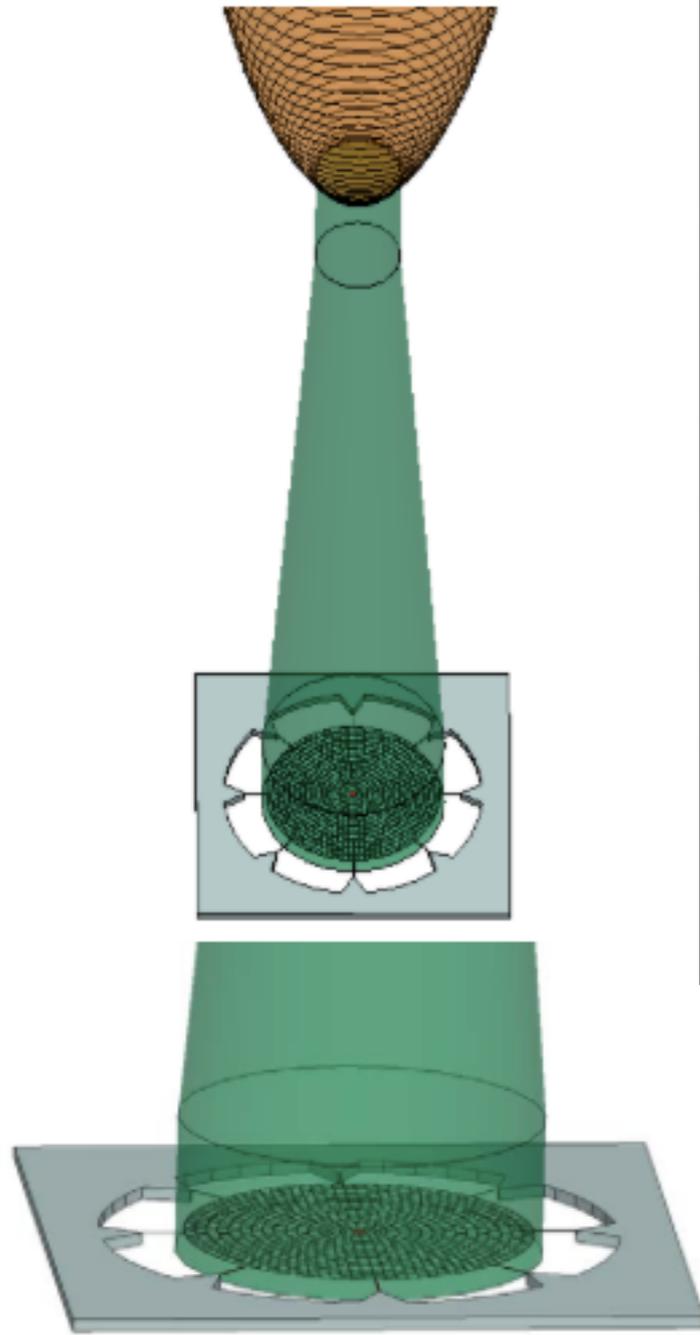
LSPE ottica



Resp: Roma1



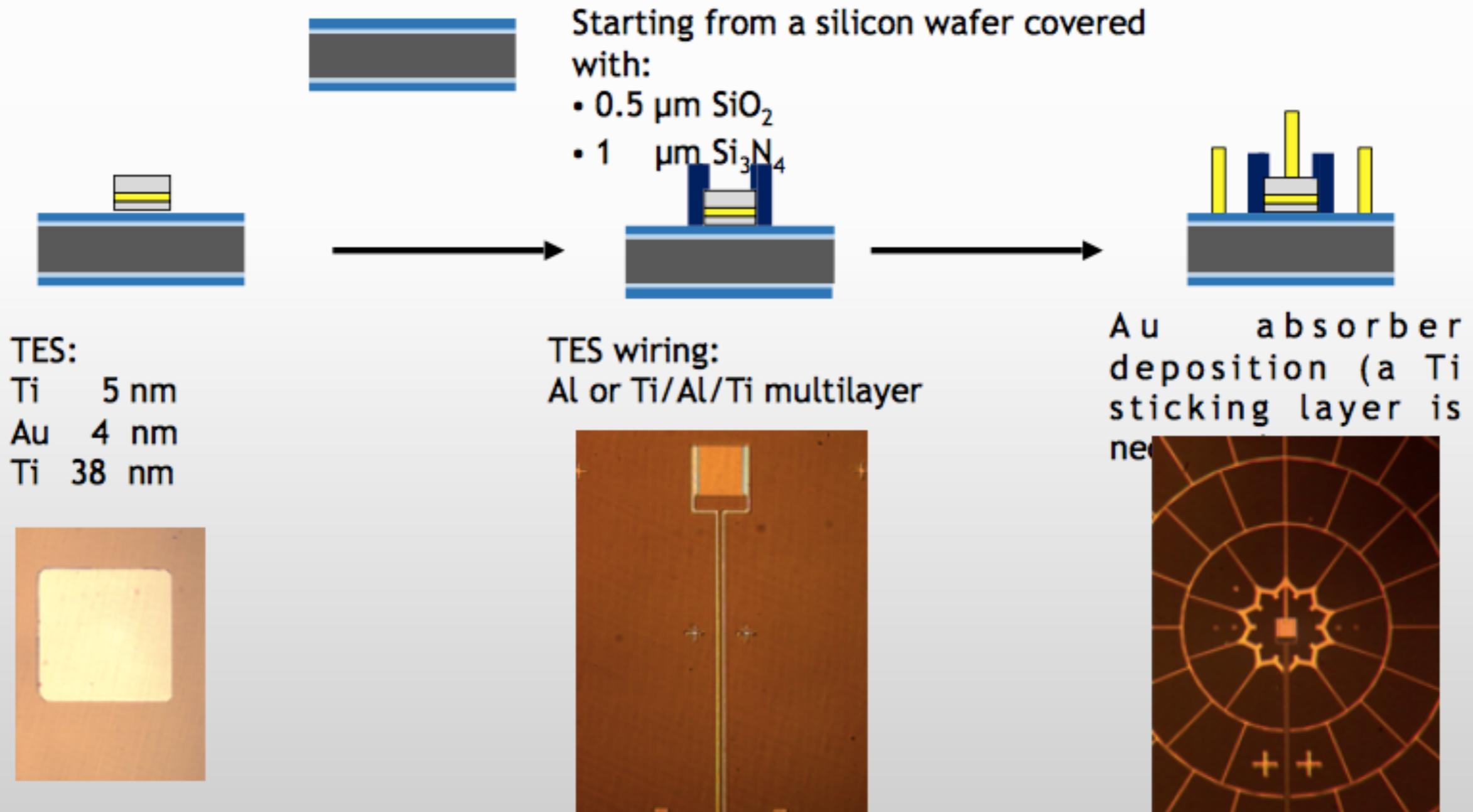
Resp: Roma1



Resp: Genova

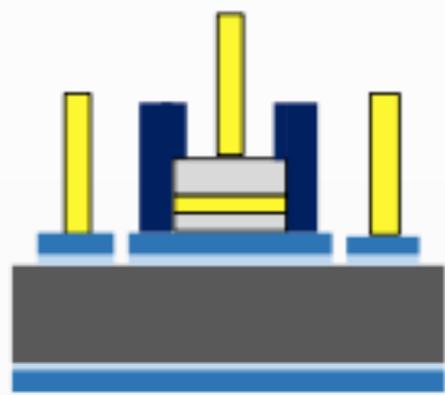
Fabrication Process 1: metals deposition

Negative Photolithography, e-beam metal evaporation, Lift-off process

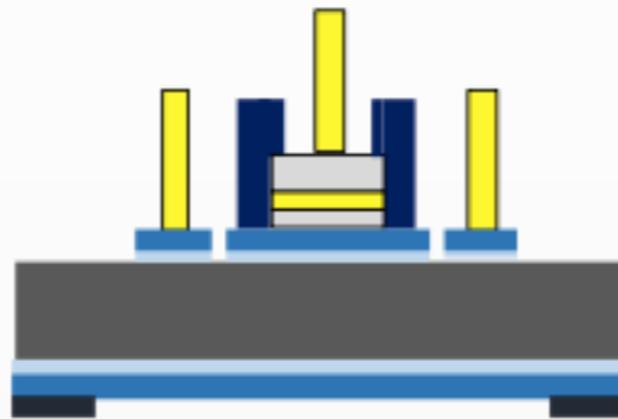


Fabrication Process 2: Etching

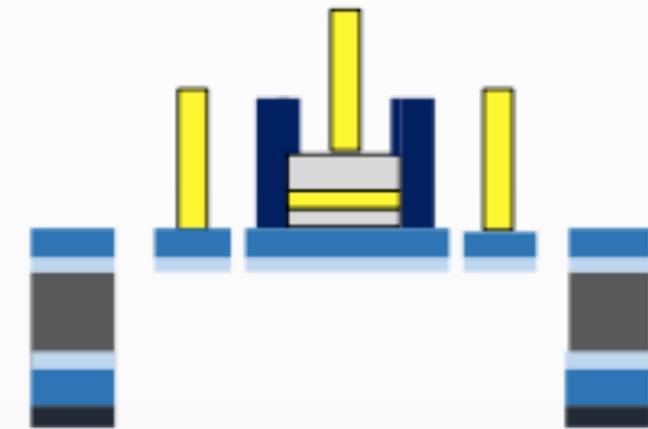
Reactive Ion Etching used to cut silicon and silicon nitride



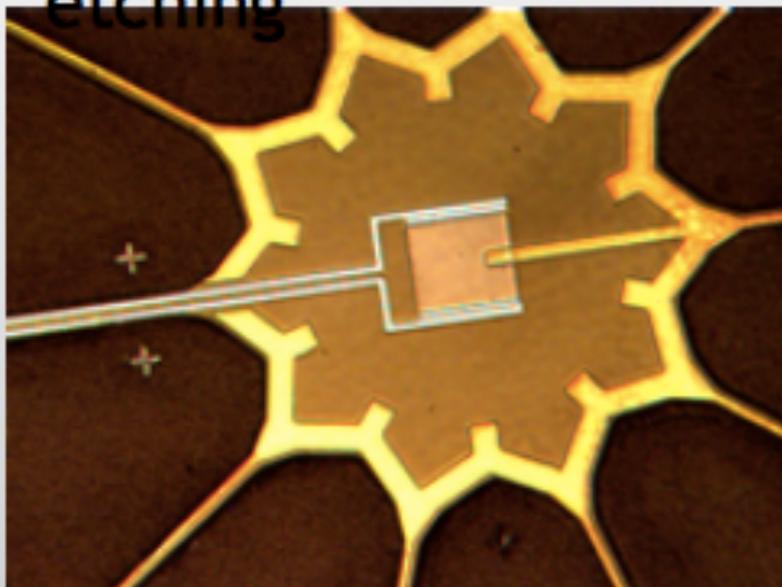
Positive
photolithography
and RIE $\text{CF}_4 + \text{O}_2$
etching



deposition of
Aluminum hard
mask on backside
with lift-off process

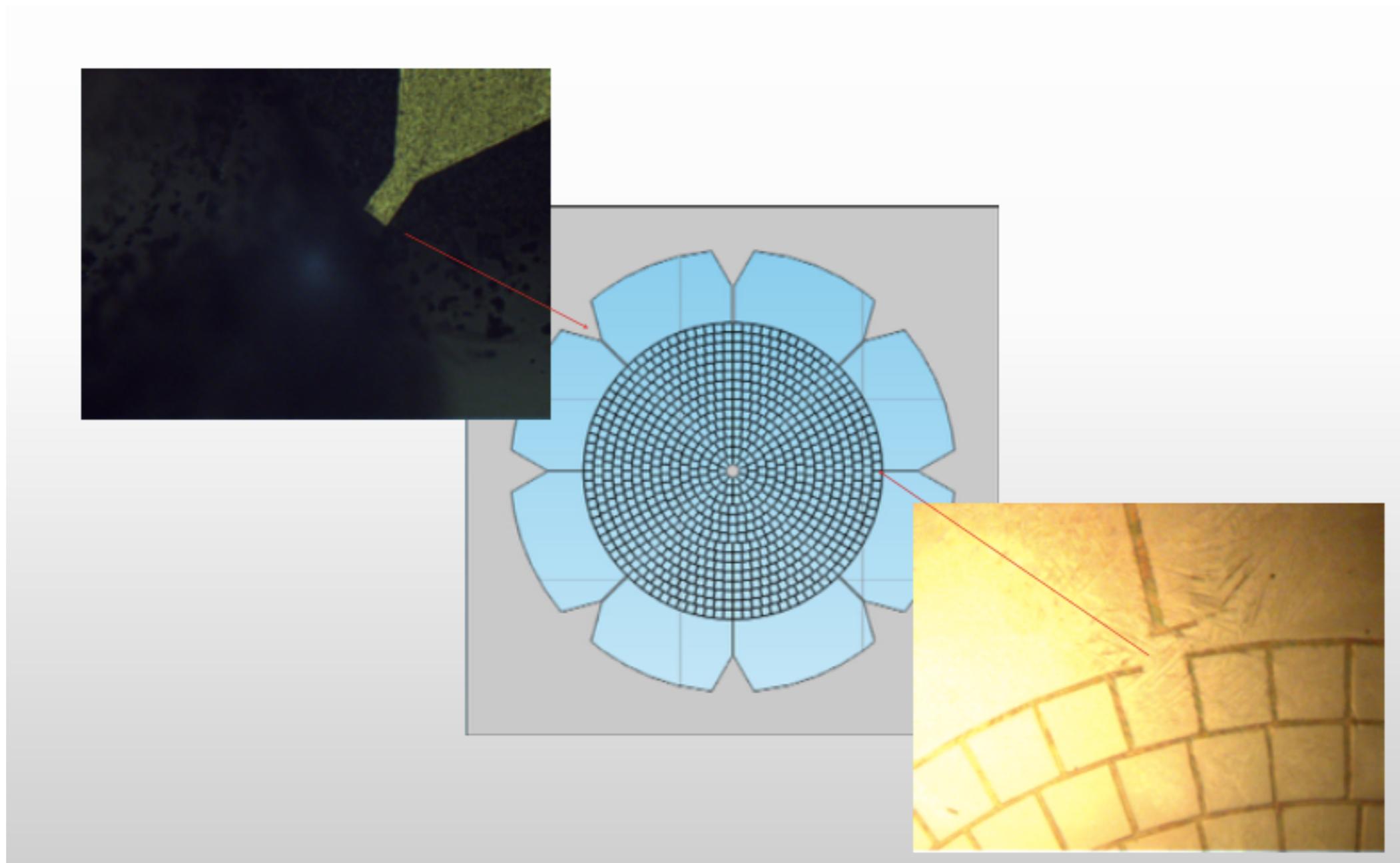


RIE back wafer etching
with $\text{SF}_6 + \text{O}_2$ and
suspension of spider
web structure

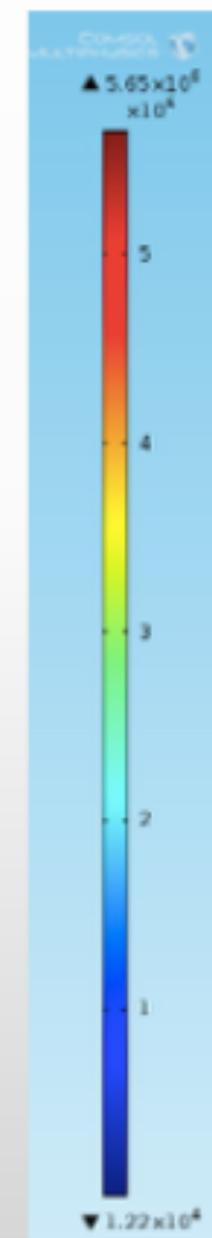
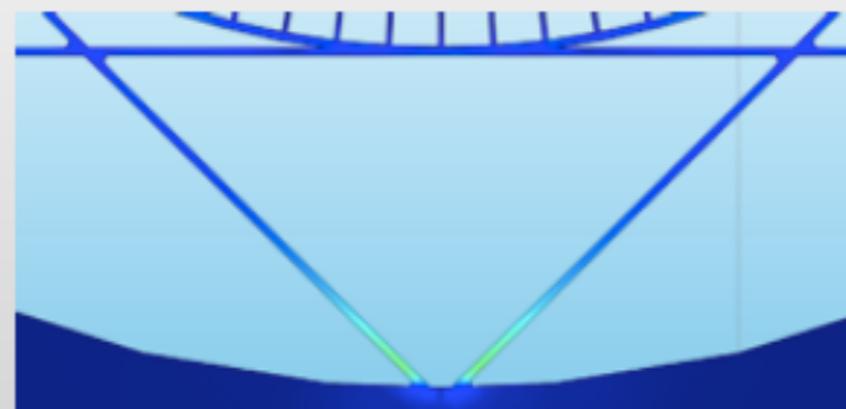
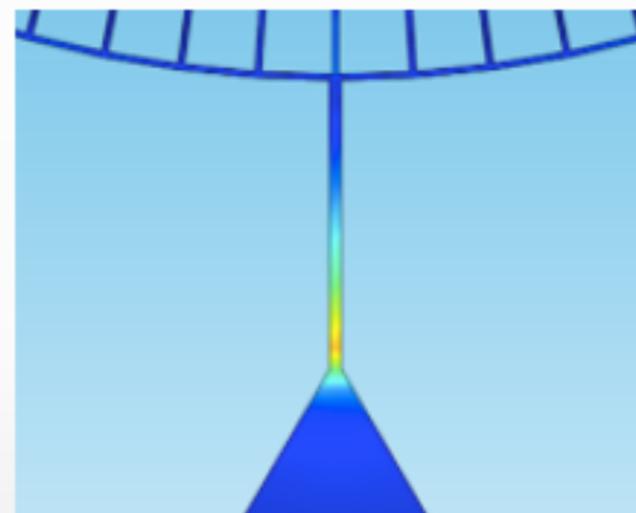
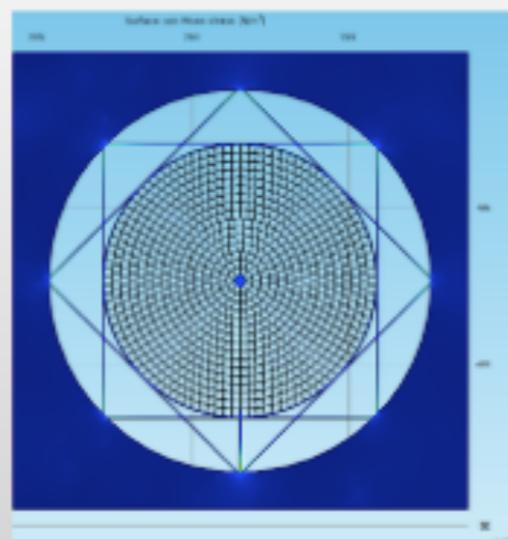
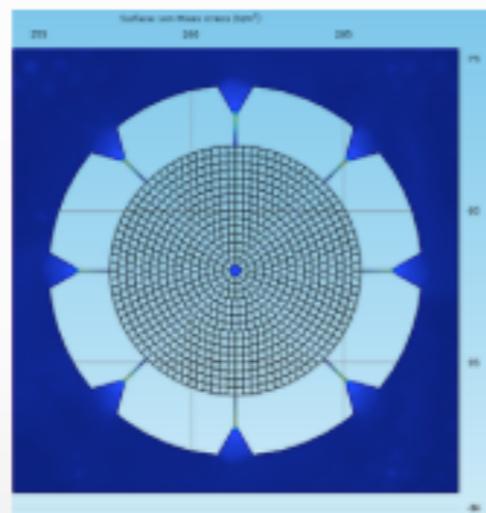


Endpoint detection by optical plasma analysis

- Con lanci nel gennai 2017 -> tempo per ottimizzare la produzione dei bolometri

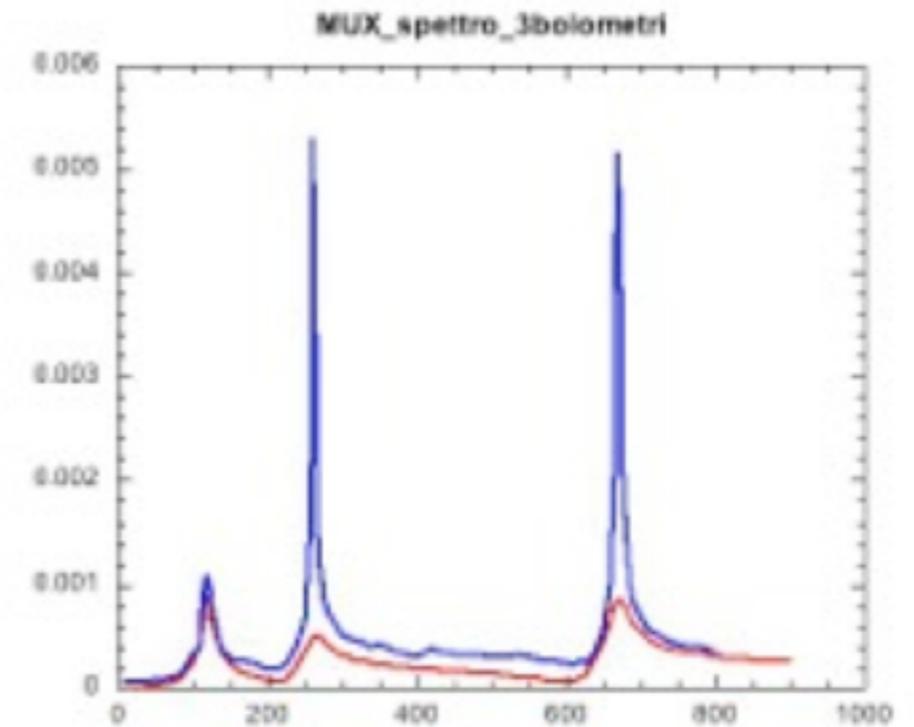
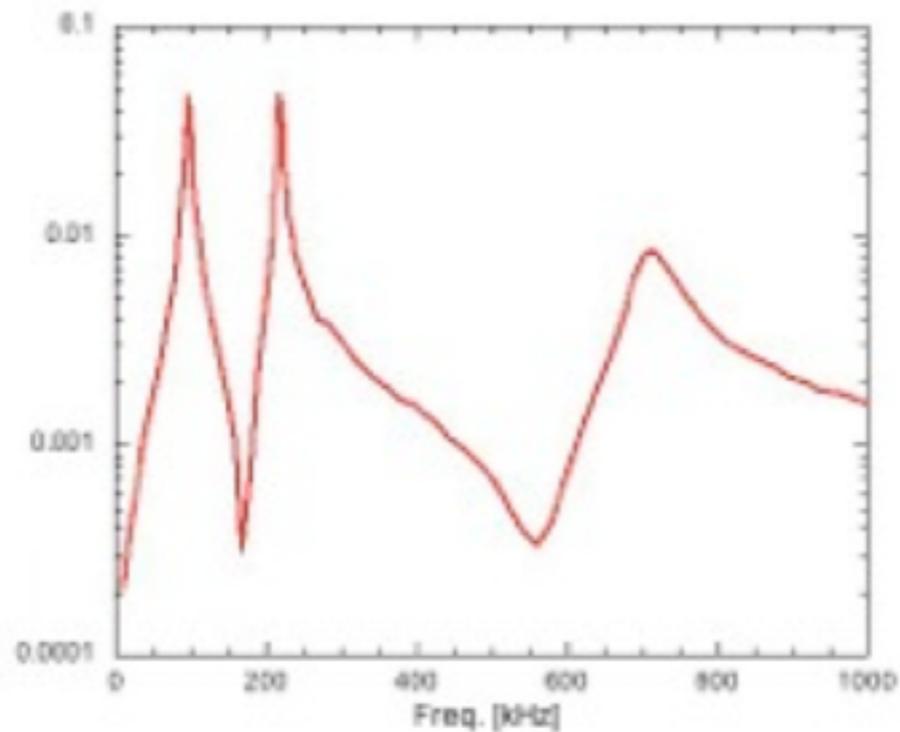
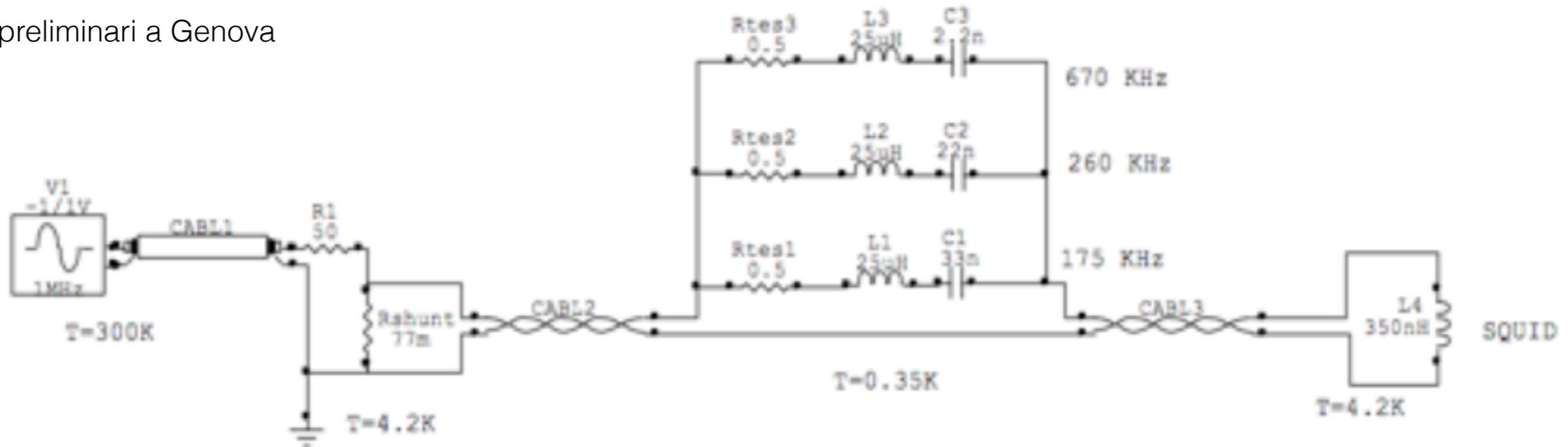


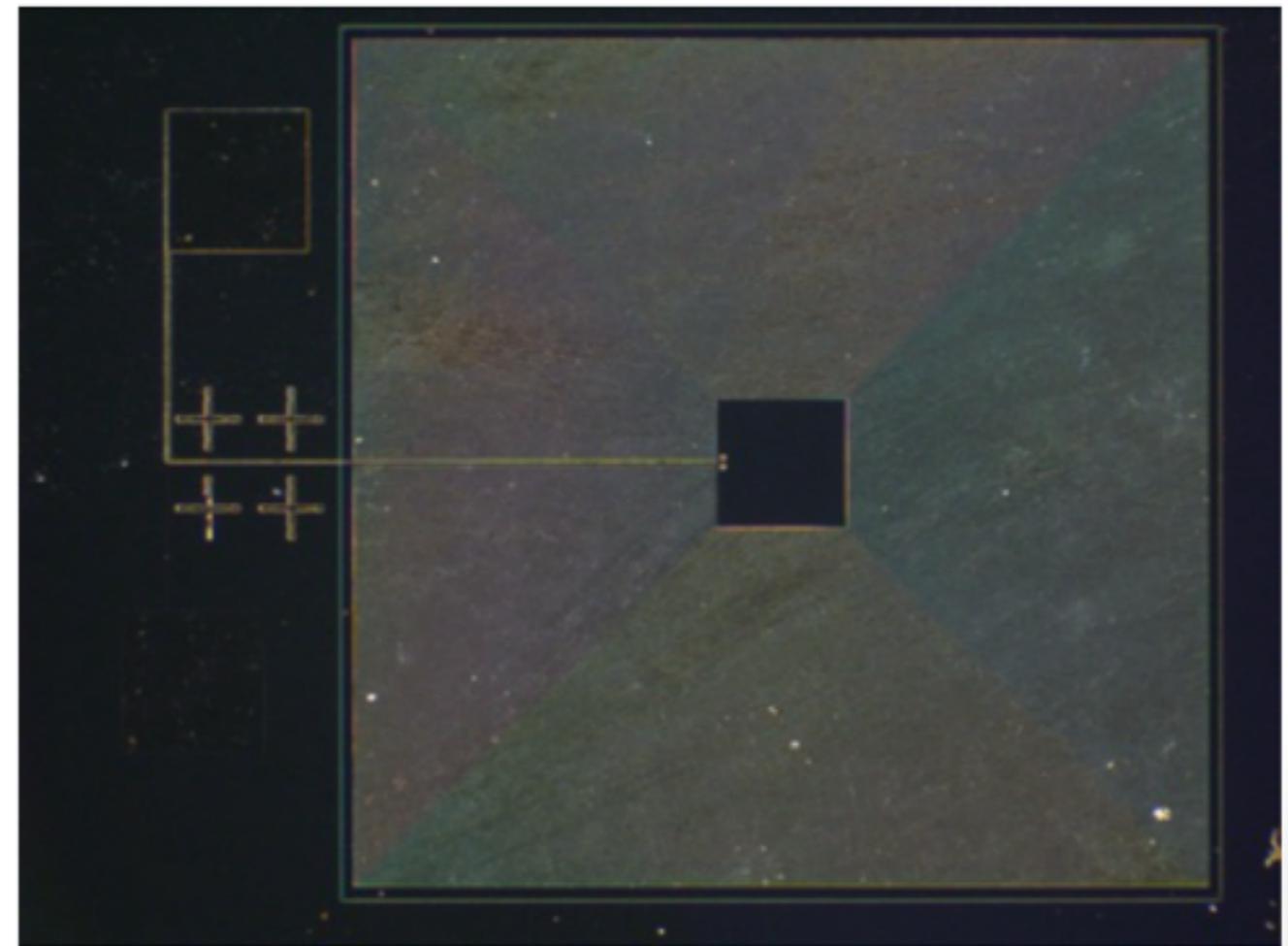
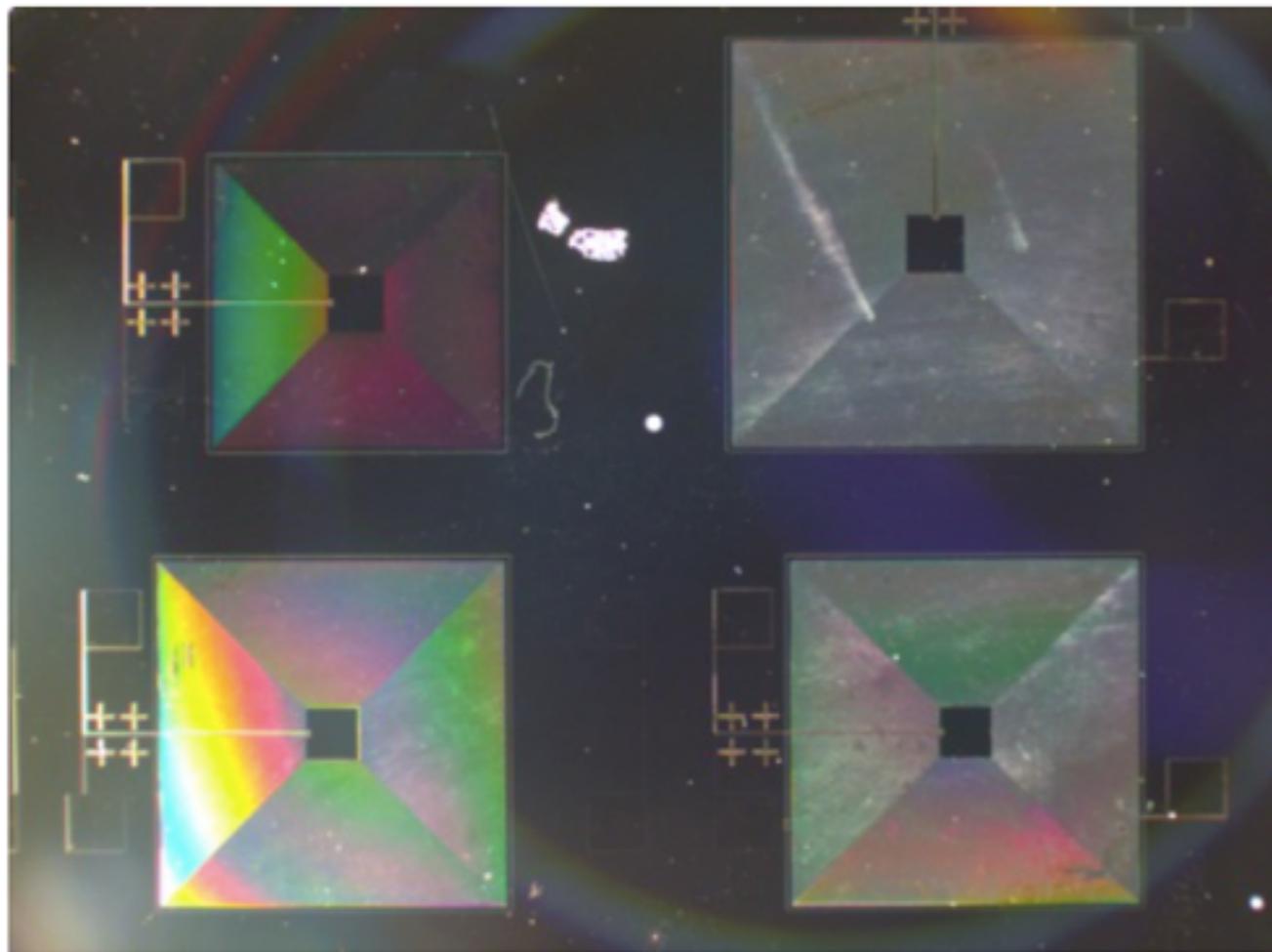
- nuova geometria delle sospensioni per ridurre lo stress e le deviazioni dalla planarita'



frequency division multiplexing 16 canali

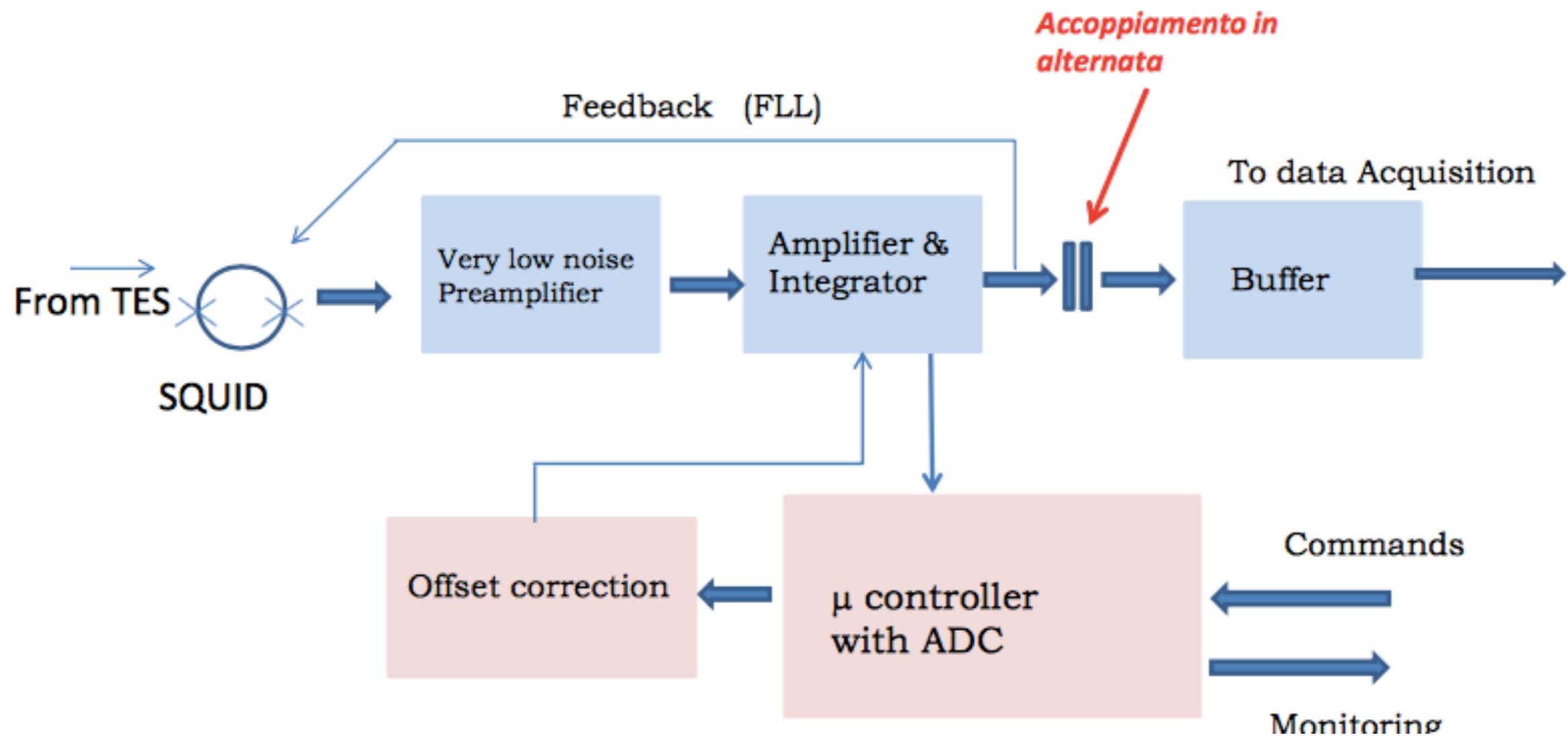
Test preliminari a Genova





Resp: Genova-Pisa

General structure of our system:



Resp: Genova

Preamplifier with FET input stage

- High gain $G=200$
- Wide bandwidth ($>2\text{MHz}$ @ 3 dB)
- Low Noise ($0.6\text{-}0.7 \text{ nV}/\sqrt{\text{Hz}}$)
(equivalente ad una resistenza di 25Ω)

- Differential input amplifier with cascode configuration to increase bandwidth and lower input capacitance (Miller effect)

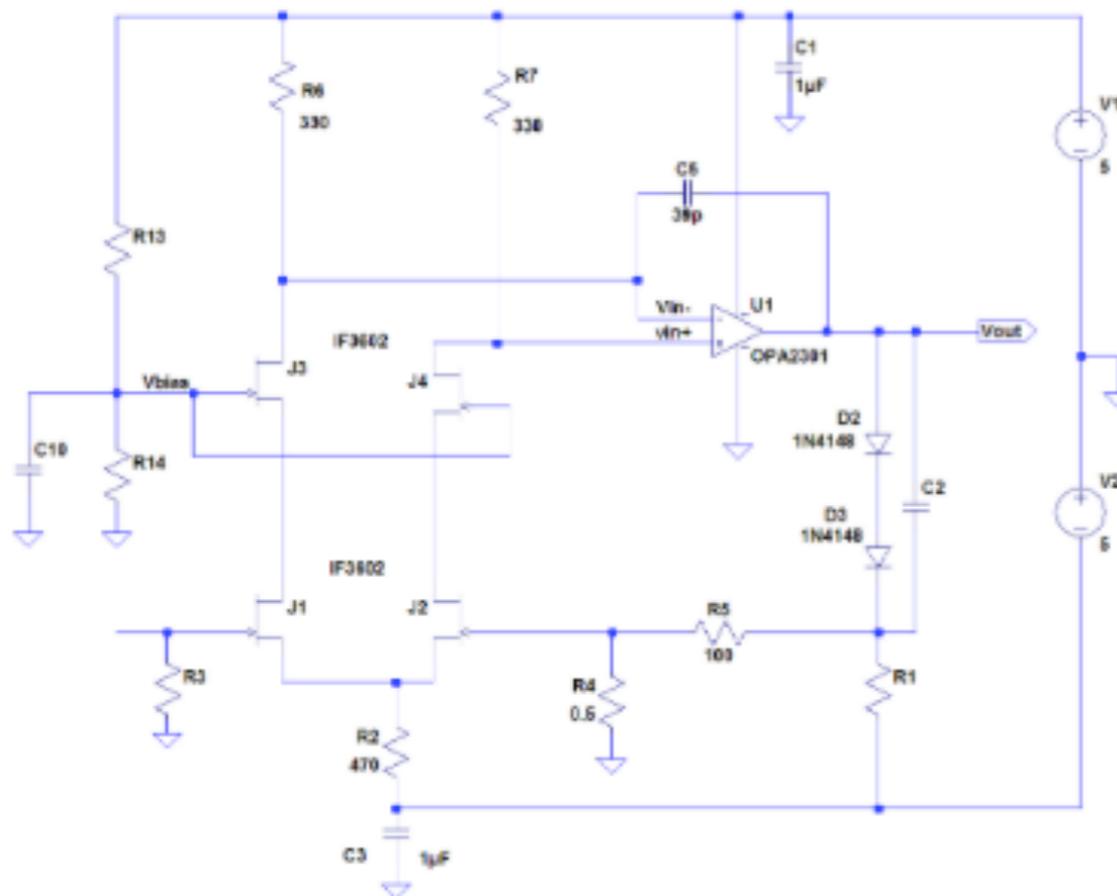
- CMOS second stage with moderate low noise ($3 \text{ nV}/\sqrt{\text{Hz}}$ nominal)

- Output offset voltage must be zeroed in the second stage.

- It must stay reasonably close to the squid: cable inductance and input capacitance can resonate in the middle of our useful bandwidth.

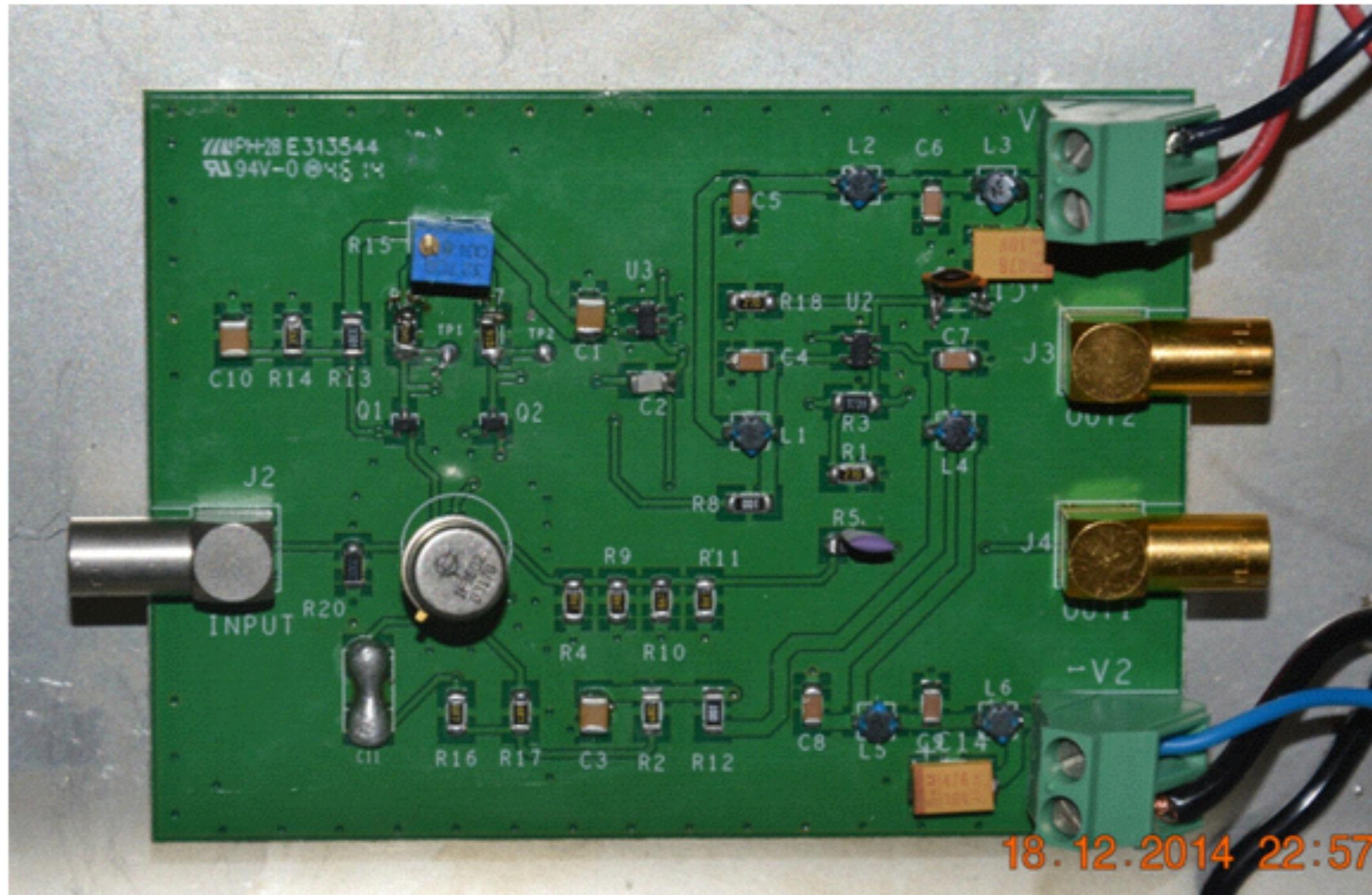
- Tested @ -100 C

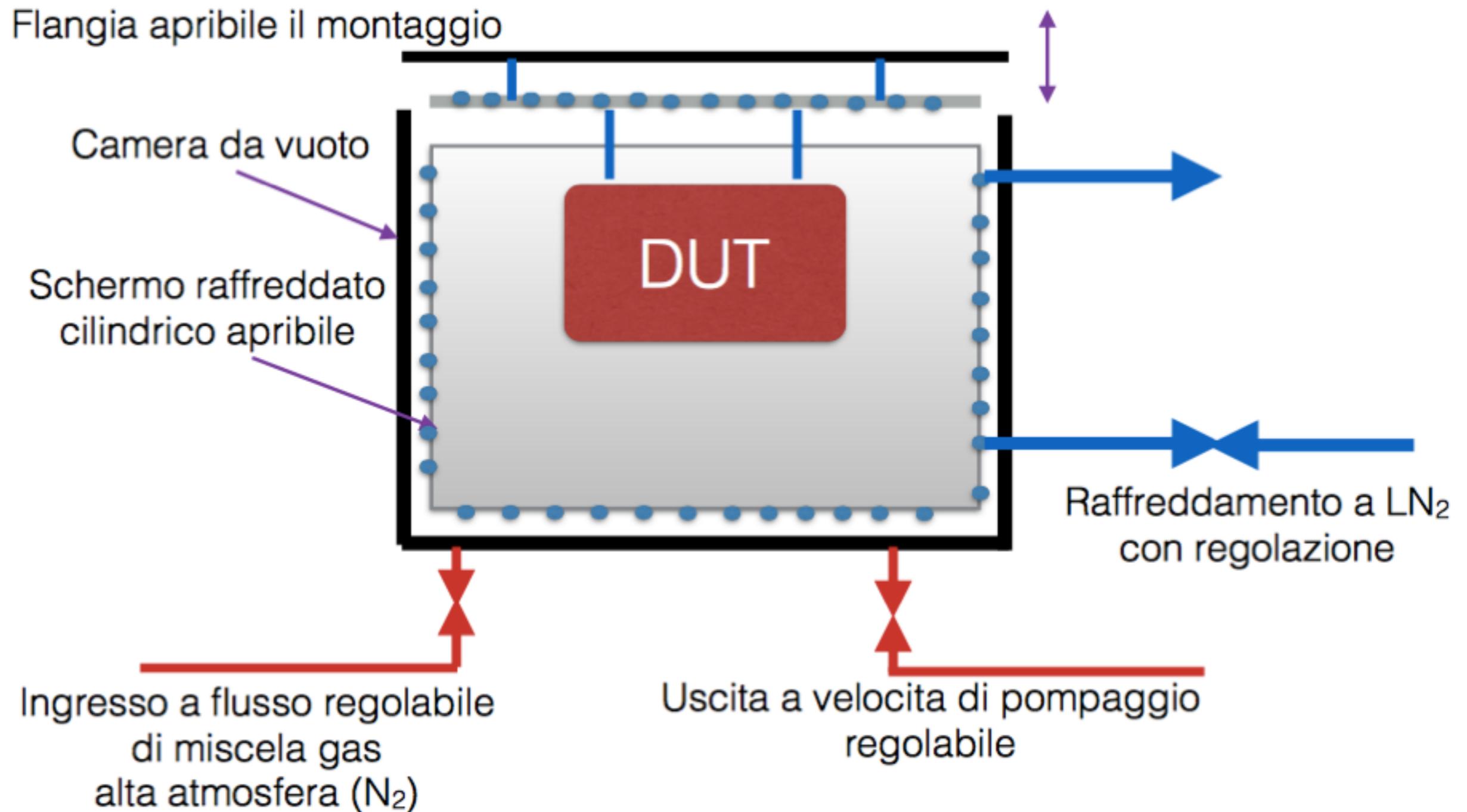
- High input capacitance ($\sim 500 \text{ pF}$)



Resp: Genova

- J-FET-CMOS cold LNA (-100 C -> temp. ambiente) F.Fontanelli





Anagrafica

Anagrafica LSPE

	LSPE
Gatti F	50
Biasotti M	40
Corsini D	80
F.Fontanelli	30
Boragno	40
totali FTE	2.4

Contributi significativi

M Biasotti : Bolometri
 L. Parodi : Criogenia, Camera Climatica
 F. Fontanelli: LNA
 D. Grosso: Camera Climatica

Impegni servizi

EXP	JANUARY	FEBRUARY	MARCH	APRIL	MAY	JUNE	JULY	SEPTEMBER	OCTOBER	NOVEMBER	DECEMBER
LSPE	Off. Mec.: Vacuum & Bolometer test support + integration @ LNF + Svalbard					3 mu					
Strutt Timing Counter Commissioning	Dis. Mec: Vacuum & Bolometer test support + integration @ LNF					3 mu					